CLAIMS

What is claimed is:

1. An electro-optic device comprising:

an electro-optic material disposed between a pair of substrates;

means for applying an electric field to the electro-optic material;

an underlying conductive layer including a conductive metal oxide laminated on one of the substrates;

a reflective conductive layer formed of one of silver and a silver alloy laminated on the underlying conductive layer; and

a transparent conductive layer laminated on the reflective conductive layer and the underlying conductive layer;

wherein the transparent conductive layer is thinner than the underlying conductive layer.

2. An electro-optic device comprising:

an electro-optic material disposed between a pair of substrates; and

means for applying an electric field to the electro-optic material;

wherein the electro-optic material is sealed in a material-sealed region in which a reflecting electrode is formed on one of the substrates, the reflecting electrode having a laminated structure including:

an underlying conductive layer formed of a conductive metal oxide laminated on one of the substrates;

a reflective conductive layer formed of one of silver and a silver alloy laminated on the underlying conductive layer; and

a transparent conductive layer laminated on the reflective conductive layer and the underlying conductive layer; and

external wiring provided outside the material-sealed region to conductively connect to the reflecting electrode, the external wiring comprising the same material layer as at least one of the underlying conductive layer and the underlying conductive layer and the transparent conductive layer of the laminated structure;

wherein the transparent conductive layer is thinner than the underlying conductive layer.

3. The electro-optic device of claim 1, wherein the transparent conductive layer has a thickness of 5 nm to 30 nm.

4. A method for manufacturing an electro-optic device including an electro-optic material disposed between a pair of substrates, and means for applying an electric field to the electro-optic material, the method comprising:

a step of forming an underlying conductive layer formed of a conductive metal oxide on one of the substrates;

a step of selectively forming a reflective conductive layer formed of one of silver and a silver alloy on the underlying conductive layer; and

a step of forming a transparent conductive layer on the underlying conductive layer and on the reflective conductive layer, the transparent conductive layer being thinner than the underlying conductive layer.

5. A method for manufacturing an electro-optic device including an electro-optic material disposed between a pair of substrates, and means for applying an electric field to the electro-optic material, the method comprising:

a step of forming an underlying conductive layer formed of a conductive metal oxide on one of the substrates;

a step of selectively forming a reflective conductive layer formed of one of silver and a silver alloy on the underlying conductive layer in a first region corresponding to a material-sealed region in which the electro-optic material is sealed;

a step of forming a transparent conductive layer on the reflective conductive layer and the underlying conductive layer in the first region and on the underlying conductive layer in a second region out of the material-sealed region, the transparent conductive layer being thinner than the underlying conductive layer; and

a step of simultaneously patterning the underlying conductive layer and the transparent conductive layer.

6. The method for manufacturing an electro-optic device of claim 4, wherein the transparent conductive layer has a thickness of 5 nm to 30 nm.

7. An electronic apparatus comprising the electro-optic device of claim 1, and control means for controlling the electro-optic device.

8. The electro-optic device of claim 2, wherein the transparent conductive layer has a thickness of 5 nm to 30 nm.

9. The method for manufacturing an electro-optic device of claim 5, wherein the transparent conductive layer has a thickness of 5 nm to 30 nm.

10. An electronic apparatus comprising the electro-optic device of claim 2, and control means for controlling the electro-optic device.